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Assignment of the vibrational spectra of the parent polysilsesquioxane (POSS): octahydridosilasequioxane, H₈Si₈O₁₂.

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Abstract

Polysilsesquioxanes (POSS) are molecules with the empirical formula (RSiO_{1.5})_n where R is a hydrogen atom or hydroxyl or an organic moiety such as an alkyl, alkene, acrylate or epoxide. The silicon atoms occupy the corners of a cube and oxygen atoms are located on the edges, the versatility of silsesquioxanes arises from the vacant fourth position of silicon. The choice of substituent enables a wide variety of properties to be engineered in a straightforward manner. The parent POSS is octasilsesquioxane, $H_8Si_8O_{12}$, with R = H and n = 8. The present work employs periodic density functional theory calculations in conjunction with *all* the available vibrational (infrared, Raman and inelastic neutron scattering) spectra to generate a complete assignment of all the modes of the parent POSS octasilsesquioxane and some of its isotopomers for both the free, (O_h) , molecule and the solid state material (C_{3i} site symmetry) including the forbidden and very weak modes. The latter are of interest because in less symmetrical silsesquioxanes, these modes will be activated.

1. INTRODUCTION

Polysilsesquioxanes (POSS) are molecules with the empirical formula $(RSiO_{1.5})_n$ where R is a hydrogen atom or hydroxyl or an organic moiety such as an alkyl, alkene, acrylate or epoxide [1], see Fig. 1. It can be seen that silicon atoms occupy the corners of a cube and oxygen atoms are located on the edges, the versatility of silsesquioxanes arises from the vacant fourth position of silicon. The choice of substituent enables a wide variety of properties to be engineered in a straightforward manner [2]. These include solubility in water or organic solvents, the ability to be blended into many polymers and, unlike most silicones or fillers, POSS molecules contain organic substituents on their outer surfaces, making them compatible or miscible with most polymers. The range of properties can be extended by choosing a reactive R substituent that can be polymerised to make true organic-inorganic hybrid polymers or eliminated to form mesoporous silicates with a well-defined cage structure. POSS molecules can thus be viewed as very small, perfectly monodisperse silica nanoparticles, with typical diameters on the order of 1-3 nm.

The parent POSS is octasilsesquioxane, $H_8Si_8O_{12}$, see Fig. 1, with R = H and n = 8, and was first synthesised in very low yield in 1959 [3], more efficient routes are now available and higher POSS with n=12,14,16 and 18 have also been synthesised and characterised [4]. The reactivity of $H_8Si_8O_{12}$ can be understood as occurring *via* a pentacoordinate Si intermediate and this helps explain why substitution in compounds with R = alkyl or aryl is difficult or impossible because of steric hindrance in the intermediate [5]. The solid state structure of $H_8Si_8O_{12}$ has been determined several times, the most relevant is the neutron diffraction study by Törnroos [6]. The space group is trigonal $R\overline{3}$ (no. 148), there is one molecule in the primitive unit cell that occupies a site of C_{3i} symmetry. The ideal molecular symmetry is octahedral, O_h , and the distortion from this is small.

The vibrational spectroscopy of octasilsesquioxane has been investigated several times over the years [7-12]. The near-octahedral symmetry of the molecule means that there are many modes that are either forbidden or very weak in both the infrared and Raman spectra. To observe these modes the inelastic neutron scattering (INS) spectrum was recorded [10]. INS spectroscopy [13] is highly complementary to infrared and Raman spectroscopy, for octasilsesquioxane the attribute that there are no selection rules and all modes are allowed was the main motivation. The vibrational structure of octahedral $H_8Si_8O_{12}$ was investigated in detail, and a harmonic force field in terms of internal force constants was determined, based on infrared, FT-Raman and INS data and on a normal coordinate analysis of $H_8Si_8O_{12}$ and $D_8Si_8O_{12}$. Group frequencies were assigned according to a potential energy analysis and relations to group frequencies of comparable silicon compounds were discussed. Based on the force field, the lowest internal torsional frequency was estimated to be 41 cm⁻¹. [7-10].

The molecular vibrations have also been assigned by periodic density functional theory (DFT) [14]. While DFT usually provides very reliable vibrational assignments, particularly when combined with INS data (e.g. [15-19]) as was done for octamethylsilsesquioxane [20], Schutte and Pretorius [14] only considered infrared data. Furthermore, inspection of their phonon dispersion curves shows multiple imaginary modes with large energies (up to 7 THz

 $= 230 \text{ cm}^{-1}$) across most of the Brillouin zone. This is indicative of a major flaw in the computational work.

The purpose of the present work is to use periodic density functional theory calculations in conjunction with *all* the available vibrational (infrared, Raman and inelastic neutron scattering (INS)) spectra to generate a complete assignment of all the modes including the forbidden and very weak modes. The latter are of interest because in less symmetrical silsesquioxanes, these modes will be activated.

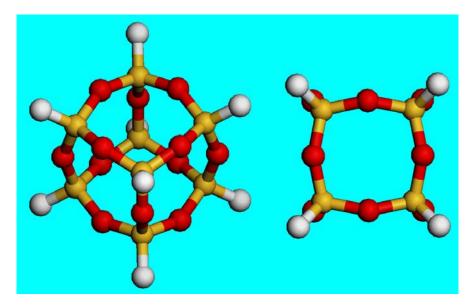


Fig. 1. Two views of the parent POSS, octasilsesquioxane $H_8Si_8O_{12}$, with O_h symmetry. Terminal atoms are hydrogen, twofold bridging are oxygen and fourfold coordinated are silicon.

2. COMPUTATIONAL STUDIES

The structure of octasilsesquioxane as determined by neutron diffraction [6] was downloaded from the Inorganic Chemical Structure Database (ICSD, datacode 75244). Periodic density functional theory (periodic-DFT) calculations were carried out using the plane wave pseudopotential method as implemented in the CASTEP code [21,22]. Exchange and correlation were approximated using the PBE functional [23]. The plane-wave cut-off energy was 770 eV. Brillouin zone sampling of electronic states was performed on 3×3×1 Monkhorst-Pack grid. The equilibrium structure, an essential prerequisite for lattice dynamics calculations was obtained by BFGS geometry optimization after which the residual forces were converged to zero within ± 0.0055 eV Å⁻¹. Phonon frequencies were obtained by diagonalisation of dynamical matrices computed using density-functional perturbation theory [24] and also to compute the dielectric response and the Born effective charges, and from these the mode oscillator strength tensor and infrared absorptivity were calculated. Raman activities were computed using a hybrid method combining density functional perturbation theory with finite displacements [24]. In addition to the calculation of transition energies and intensities at zero wavevector, phonon dispersion was also calculated along high symmetry directions throughout the Brillouin zone. For this purpose, dynamical matrices were computed on a regular grid of wavevectors throughout the Brillouin zone and Fourier interpolation was used to extend the computed grid to the desired fine set of points along the high-symmetry paths [25]. Transition energies for isotopic species were calculated from the dynamical matrix that is stored in the CASTEP checkpoint file using the PHONONS utility [26] The atomic displacements in each mode that are part of the CASTEP output (.phonon files) are also all that is required to generate the INS spectrum using the program ACLIMAX [27]. Visualization of the modes to aid assignments was carried out with Jmol [28]. The .phonon files and a description of how to use Jmol to visualise the modes are included in the Supporting Information. The INS spectrum of octasilsesquioxane was that reported from previously [10] and is available the INS database at: http://wwwisis2.isis.rl.ac.uk/INSdatabase/.

3. RESULTS AND DISCUSSION

The idealised structure of the gas phase molecule is O_h and this is observed experimentally by gas phase electron diffraction [29]. In the crystal the symmetry is reduced to C_{3i} , Table 1 shows the correlation from O_h to C_{3i} . It can be seen that there are a large number of modes that are inactive in the free molecule, whereas all the modes are allowed by either infrared or Raman spectroscopy in the solid state. However, a mode may be allowed but have vanishingly small intensity, this may be expected to be the case for the free-molecule forbidden modes that are activated in the solid state. Note that all the modes are allowed for INS spectroscopy

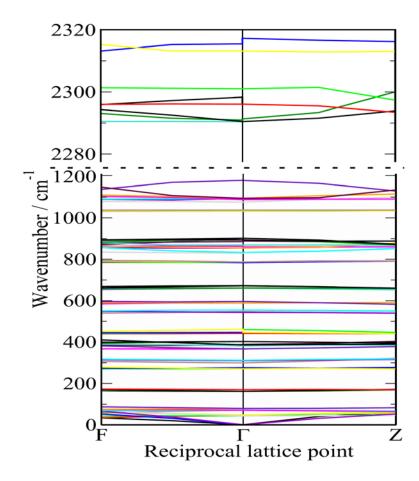


Fig. 2. Calculated dispersion curves for the primitive unit cell of octasilsesquioxane showing all real modes across the entire Brillouin zone. Note the change of scale at 1200 cm⁻¹. The data have not been scaled.

Fig. 2 shows the dispersion curves calculated for the solid state structure of octasilsesquioxane. In contrast to [14], the modes are all real across the entire Brillouin zone, as expected for a stable structure. (The discontinuities at the Γ -point are due to longitudinal optical transverse optical (LOTO) splitting).

Fig. 3 compares the experimental INS spectrum of octasilsesquioxane [10], 3a, with that generated from the calculation of the free molecule with O_h symmetry, 3b, and the full dispersion calculation of the solid state structure, 3c. (In both 3b and 3c, the region 0 – 2000 cm⁻¹ has been scaled by 1.03). It can be seen that both structures fit the data very well, thus validating the calculations. As would be expected, the match of the experimental data to the solid state structure is marginally better, particularly in the lattice mode region.

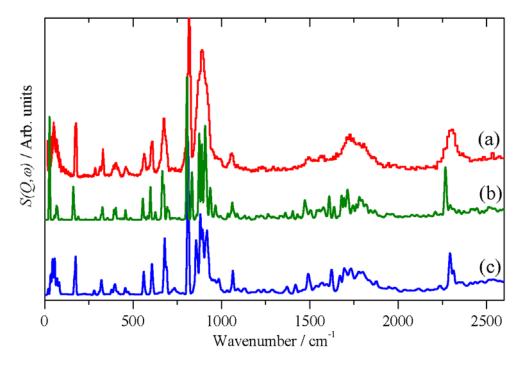


Fig. 3. Comparison of: (a) the experimental INS spectrum of octasilsesquioxane [10] and that generated from the CASTEP calculation of (b) the free molecule with O_h symmetry and (c) the solid state with C_{3i} site symmetry. In (b) and (c) the 0 – 2000 cm⁻¹ region has been scaled by 1.03.

Table 2 lists the observed and calculated transition energies and intensities for the free molecule and the solid state. The splitting of the *T* modes into *A* and *E* components by the reduction in the molecular symmetry from O_h to C_{3i} is visible for most of the modes in the infrared spectrum, *e.g.* 875 (T_{1u}) \rightarrow 882 (E_u) and 861 (A_u) cm⁻¹. It is noted that the calculated infrared intensity of the E_u modes is approximately twice that of the A_u modes, as suggested in [11], validating their assignments of the E_u and A_u components.

It was proposed [11] that the infrared active modes fall into two classes that depend on whether the motion is largely tangential or radial. The correlation crucially depends on whether modes 27 and 29 are described as radial and tangential respectively, as suggested in [11], or tangential and radial respectively as assigned previously [7-10]. (The mode

numbering is that used previously [7-11] and is given in Table S1 of the Supplementary Information). As may be seen from Fig. 4, neither description is accurate, in both cases the silicon and hydrogen atoms on the threefold axis move radially, while the other atoms move tangentially. The difference in the modes is the relative phases of the motions. (Animations of the modes can be seen using Jmol [28], see the Supplementary Information for details).

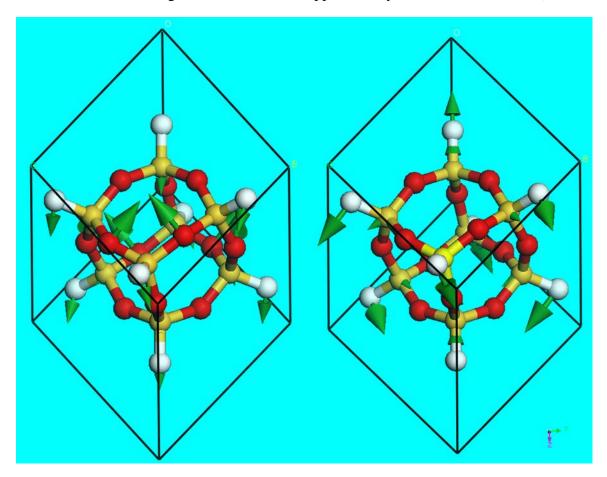


Fig. 4. Displacements of the atoms in the A_u component of modes 27 (left) and 29 (right). Terminal atoms are hydrogen, twofold bridging are oxygen and fourfold coordinated are silicon.

Experimental data is available for most of the infrared and Raman active modes of $D_8Si_8O_{12}$ and a few of the modes of $HD_7Si_8O_{12}$ (present as an impurity in $D_8Si_8O_{12}$) [8,9]. For $HD_7Si_8O_{12}$ as a free molecule (*i.e.* O_h symmetry in the H_8 or D_8 parent), there is only one isotopomer because all the sites are identical under O_h symmetry. This has C_{3v} symmetry and the correlation is given in Table 1. For the solid state C_{3i} species, there are two isotopomers depending on whether the Si–H is bond lies along the threefold axis or not, these have C_3 and C_1 site symmetry respectively. The correlation for the C_3 species is the same as for C_{3i} except that the g and u subscripts are omitted (since the centre of symmetry is destroyed by the isotopic substitution) and all modes are allowed in both the infrared and Raman spectrum, as is also the case for C_1 site symmetry. CASTEP allows the ready calculation of isotopomers *via* the PHONONS utility [26] and the results are given in Table 3. It can be seen that the agreement is generally excellent.

4. CONCLUSIONS

This study provides a complete assignment of the vibrational spectra of the parent POSS octasilsesquioxane and some of its isotopomers for both the free, (O_h) , molecule and the solid state material (C_{3i} site symmetry). The combination of infrared, Raman and INS spectroscopic data from the literature has enabled most of the modes to be observed.

Acknowledgements

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H ₈ Si ₈ O ₁₂		HD ₇ Si ₈ O ₁₂		Primitive cell of space group $R\overline{3}$	
$O_{ m h}$	Activity ^a	C_{3v}	Activity	Site group C_{3i}	Activity
Si-H stretch	nes				
$A_{1 m g}$	R	A_1	IR/R	$A_{ m g}$	R
$T_{2 m g}$	R	$A_1 + E$	IR/R	$A_{\rm g} + E_{\rm g}$	R
A_{2u}	ia	A_1	IR/R	$A_{ m u}$	IR
T_{1u}	IR	$A_1 + E$	IR/R	$A_{\rm u} + E_{\rm u}$	IR
Framework + Si–H bend	ling				
$2A_{1g}$	R	$2A_1$	IR/R	$2 A_{\rm g}$	R
$1 A_{2g}$	ia	$1 A_2$	ia	$1 A_{ m g}$	IR
$4 E_{\rm g}$	R	4 <i>E</i>	IR/R	$4 E_{ m g}$	R
3 <i>T</i> _{1g}	ia	$3A_2 + 3E$	ia & IR/R	$3A_{\rm g} + 3E_{\rm g}$	IR
5 T _{2g}	R	$5 A_1 + E$	IR/R	$5 A_{\rm g} + 5 E_{\rm g}$	R
$2 A_{2u}$	ia	$2 A_1$	IR/R	$2 A_{\rm u}$	IR
$3 E_{\rm u}$	ia	3 E	IR/R	3 <i>E</i> _u	IR
$5 T_{1u}$	IR	$5 A_1 + 5 E$	IR/R	$5 A_{\rm u} + 5 E_{\rm u}$	IR
4 <i>T</i> _{2u}	ia	$4A_2 + 4E$	ia & IR/R	$4A_{\rm u} + 4E_{\rm u}$	IR
Libration					
	ia		ia	$A_{\rm g}+E_{\rm g}$	R
Translation					
	ia		ia	$A_{\rm u} + E_{\rm u}$	IR

Table 1: Correlation diagram and spectral activity for octasilsesquioxane from the free molecule, O_h , to the site group, C_{3i} , and also for the HD₇Si₈O₁₂ isotopomer. Note that *all* modes are allowed for INS spectroscopy.

 a IR = infrared allowed, R = Raman allowed, IR/R infrared and Raman allowed, ia = inactive in both infrared and Raman.

Table 2: Observed and calculated vibrational transition energies and intensities of octasilses quioxane for the free molecule with O_h symmetry and the solid state material with C_{3i} symmetry.

Free m	ree molecule, <i>O</i> _h					Solid state, C_{3i}							Description ^a
CAST	EP^b			Expt		CASTI	$\in \mathbf{P}^b$			Expt	t		
Sym	cm ⁻¹	IR / km mol ⁻¹	R / Å ⁴ amu ⁻ 1	IR [10] / cm ⁻¹	R [7] / cm ⁻¹	Sym	cm ⁻¹	IR / km mol ⁻¹	R / Å ⁴ amu ⁻¹	IR [11] / cm ⁻¹	R [10] / cm ⁻¹	INS [10] / cm ⁻¹	
A_{1g}	2274		1105		(2302)	$A_{ m g}$	2383		1606		2302		vs(Si-H)
T_{1u}	2269	852		2277 m		A_{u}	2382	315		2293		2300	vas(Si–H)
						E_{u}	2365	752		2274			
T_{2g}	2267		589		(2286)	$A_{ m g}$	2370		1948		2296		vas(Si–H)
						$E_{ m g}$	2359		295		2286		
A_{2u}	2265					A_{u}	2359	56					vas(Si–H)
T_{1u}	1156	5835		1141 vs		A_{u}	1129	2792		1120			vas(Si–O)
						E_{u}	1127	5892		1183			
T_{2g}	1147				(1118)	$E_{ m g}$	1127		8		1117		vas(Si-O)

						$A_{ m g}$	1121		6			
A_{2u}	1120					$A_{ m u}$	1108	41				vas(Si–O)
$T_{1 m g}$	1061					$A_{ m g}$	1068		1		1058	vas(Si–O)
						$E_{ m g}$	1064					
E_{u}	1060					$E_{ m u}$	1065	12				vas(Si–O)
$E_{ m g}$	912		21		(932)	$E_{ m g}$	929		35	932	932	δ(Si-O-H)
T_{2u}	907					$E_{ m u}$	920	16			915	δ(Si-O-H)
						$A_{ m u}$	909	110				
					(897,					897		δ(Si-O-H)
T_{2g}	889		72		883)	$A_{ m g}$	895		35			
						$E_{ m g}$	880		21	893	889	
T_{1u}	875	1443		881 s		$E_{ m u}$	858	2514	882	2	868	δ(Si-O-H)
						A_{u}	852	1346	86	1		
E_{u}	806					$E_{ m u}$	811	3			817	δ(Si-O-H)
$T_{1 m g}$	805					$A_{ m g}$	811		1	811		δ(Si-O-H)
						$E_{ m g}$	807		1		817	

$E_{ m g}$	675		44		(697)	$E_{ m g}$	692		95	697	688	vs(Si–O)
T_{2u}	666					$E_{ m u}$	681	10			675	vs(Si–O)
						A_{u}	680	3				
T_{2g}	599					$A_{ m g}$	614		2	610		vs(Si–O)
						$E_{ m g}$	606		1		607	
$A_{1 \mathrm{g}}$	568		12		(579)	$A_{ m g}$	571		52	580		δ(O-Si-O)
T_{1u}	556	57		566 w		A_{u}	563	13	568			δ(O-Si-O)
						E_{u}	560	12	557		564	
T_{1u}	457	381		465 m		A_{u}	460	222	483			δ(O-Si-O)
						$E_{ m u}$	460	534	463		459	
$A_{1\mathrm{g}}$	443		56		(456)	$A_{ m g}$	455		184	456		δ(O-Si-O)
$E_{ m g}$	413					$E_{ m g}$	415		2	423	418	δ(O-Si-O)
$T_{ m 2g}$	403				(411)	$E_{ m g}$	398		2	414	403	δ(O-Si-O)
						$A_{ m g}$	393		3			
$T_{1\mathrm{u}}$	393	435		399 s		$A_{ m u}$	378	448	400			δ(O-Si-O)

			E_{u}	378	814	389		387	
$T_{1 m g}$	328		$A_{ m g}$	321			352	329	δ(O-Si-O)
			$E_{ m g}$	319				312	
A_{2u}	319		A_{u}	309	10				δ(O-Si-O)
T_{2u}	287		A_{u}	284	9				δ(O-Si-O)
			E_{u}	279	1			286	
$T_{ m 2g}$	167	(171)	$A_{ m g}$	167		4	171	175	δ(O-Si-O)
			Eg	167		4		171	
E_{u}	162		E_{u}	175					δ(O-Si-O)
$E_{ m g}$	73	(84)	$E_{ m g}$	82		1	84	87	δ(O-Si-O)
T_{2u}	67		A_{u}	74				65	δ(O-Si-O)
			E_{u}	73					
$A_{2 m g}$	57		$A_{ m g}$	50				55	τ(O-Si-O)
			$A_{ m g}$	46				53	Libration
			$E_{ m g}$	45					

 $E_{\rm u}$ Acoustic
mode $A_{\rm u}$ 0

^{*a*} For both the $O_{\rm h}$ and $C_{\rm 3i}$ structures visualisation of the modes is possible with the use of Jmol. See the Supporting Information for details.

^{*b*} The modes at $<2000 \text{ cm}^{-1}$ have been scaled by 1.03

Table 3: Observed and calculated vibrational transition energies and intensities of isotopomers of octasilses quioxane for the free molecule with $O_{\rm h}$ symmetry and the solid state material with $C_{\rm 3i}$ symmetry.

Free m	olecule					Solid s	tate						Description ^a
CAST O _h	EP	Expt	CAST C_{3v}	ΓEP	Expt	CASTI C_{3i}	EP	Expt	CAST C ₃	ΈP	C_1	Expt	
D8			HD7			D8			HD7		HD7		
Sym	cm ⁻¹	IR [7,8] / cm ⁻¹	Sym	cm ⁻¹	IR [8] / cm ⁻¹	Sym	cm ⁻¹	R [8] / cm ⁻¹	Sym	cm ⁻¹	cm ⁻¹	R [8] / cm ⁻¹	
A _{1g}	1693		A_1	2277		$A_{ m g}$	1759	1676	Α	2374	2322	2301 2292	vs(Si–D/H)
T_{1u}	1688	1658	A_1	1693		$A_{ m u}$	1759		A	1759	1726		vas(Si–D)
			Ε	1688		$E_{ m u}$	1721		Ε	1721	1759 1759		
T_{2g}	1686		A_1	1687		$A_{ m g}$	1727	1668	A	1728	1721		vas(Si–D)
			Ε	1686		$E_{ m g}$	1717	1660	Ε	1717	1717 1717		
A_{2u}	1684		A_1	1685		$A_{ m u}$	1716		A	1717	1719		vas(Si–D)

T_{1u}	1155	1140	Ε	1154	$E_{ m u}$	1118	E	1123	1123 1123		vas(Si–O)
			A_1	1154	$A_{ m u}$	1116	A	1118	1119		
T_{2g}	1146		A_1	1146	$E_{ m g}$	1123	Ε	1119	1118 1118		vas(Si–O)
			Ε	1145	$A_{ m g}$	1117	1115 A	1116	1116		
A_{2u}	1119		A_1	1118	$A_{ m u}$	1101	A	1101	1101		vas(Si–O)
T_{1g}	1041		Ε	1048	$A_{ m g}$	1044	A	1044	1051		vas(Si–O)
			A_2	1041	$E_{ m g}$	1042	E	1050	1049 1043		
E_{u}	1040		Ε	1039	$E_{ m u}$	1042	E	1042	1042 1042		vas(Si–O)
$E_{ m g}$	801		Ε	878	Eg 881	817	Ε	872	884 876	885 877	δ(Si-O-D/H)
T_{2u}	789		Ε	797	E _u 839	802	Ε	811	812 809		δ(Si-O-D)
			A_2	789	$A_{ m u}$	795	A	795	800		
T_{2g}	724		Ε	765	770 $A_{ m g}$	729	729 A	730	716	764	δ(Si-O-D)
			A_1	724	720 $E_{\rm g}$	711	713 E	769	774		

									765	
T_{1u}	683	687	Ε	707	710 A_{u}	670	Α	670	660	δ(Si-O-D)
			A_1	684	$E_{ m u}$	659	Ε	696	702 694	
Eu	606		Ε	651	E _u 658	607	E	645	649 640	δ(Si-O-D)
$T_{1\mathrm{g}}$	605		Ε	606	$A_{ m g}$	607	A	607	604	δ(Si-O-D)
			A_2	605	$E_{ m g}$	603	E	606	607 606	
$E_{ m g}$	548		Ε	570	$E_{ m g}$	563	562 E	581	585 578	vs(Si–O)
T_{2u}	546		A_1	562	$E_{ m u}$	560	E	561	564 562	vs(Si–O)
			Ε	547	$A_{ m u}$	566	Α	567	560	
T_{2g}	528		A_2	546	$A_{ m g}$	558	541 A	559	559	vs(Si–O)
			Ε	532	$E_{ m g}$	548	Ε	551	548 549	
$A_{1\mathrm{g}}$	561		A_1	529	$A_{ m g}$	546	579 A	547	553	δ(O-Si-O)
T_{1u}	522	531	A_1	524	$A_{ m u}$	525	A	526	527	δ(O-Si-O)

			Ε	523	$E_{ m u}$	534	E	535	535 536	
T_{1u}	447		Ε	449	$A_{ m u}$	464	A	473	473	δ(O-Si-O)
			A_1	448	$E_{ m u}$	466	E	466	466 466	
$A_{1\mathrm{g}}$	440		A_1	441	$A_{ m g}$	473	452 A	464	464	δ(O-Si-O)
$E_{ m g}$	413		Ε	412	$E_{ extsf{g}}$	416	E	417	417 417	δ(O-Si-O)
$T_{2 m g}$	395		Ε	397	$E_{ m g}$	405	E	405	405 405	δ(O-Si-O)
			A_1	396	$A_{ m g}$	401	405 A	402	401	
$T_{1\mathrm{u}}$	386	391	Ε	385	$A_{ m u}$	379	Ε	384	384 383	δ(O-Si-O)
			A_1	384	$E_{ m u}$	383	A	379	380	
T_{1g}	322		Ε	321	$A_{ m g}$	313	351 A	314	315	δ(O–Si–O)
			A_2	320	$E_{ extsf{g}}$	305	E	306	306 305	
A_{2u}	314		A_1	314	$A_{ m u}$	302	A	302	302	δ(O-Si-O)
T_{2u}	287		A_2	286	$A_{ m u}$	279	Α	279	280	δ(O-Si-O)

		E	286	$E_{ m u}$	271	Ε	271	271 271	
T_{2g}	166	E	166	$A_{ m g}$	166	170 A	166	166 166	δ(O–Si–O)
		A_1	166	Eg	166	Ε	166	166	
$E_{ m u}$	156	E	154	$E_{ m u}$	173	Ε	174	174 174	δ(O-Si-O)
$E_{ m g}$	73	E	75	$E_{ m g}$	101	84 E	101	101 101	δ(O-Si-O)
T_{2u}	66	A_2	64	$A_{ m u}$	104	A	104	103	δ(O-Si-O)
		E	63	$E_{ m u}$	101	Ε	101	101 101	
$A_{2\mathrm{g}}$	57	A_2	39	$A_{ m g}$	101	A	101	101	τ(O-Si-O)
				$A_{ m g}$	52	A	52	52	Libration
				$E_{ m g}$	53	Ε	53	53	
				$E_{ m u}$					Acoustic mode
				$A_{ m u}$	0				

^{*a*} The modes at $<2000 \text{ cm}^{-1}$ have been scaled by 1.03